UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.usplo.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/642,611	08/19/2003	Toshitaka Aoyagi	402761	2829	
23548	7590 01/22/2007		EXAMINER		
	T & MAYER, LTD ENTH ST. NW		VAN ROY, TOD THOMAS ART UNIT PAPER NUMBER	OD THOMAS	
SUITE 300	ON, DC 20005-3960		ART UNIT PAPER NUMBER		
WASHINGTO	714, DC 20003-3700		. 2828		
SHORTENED STATUTO	RY PERIOD OF RESPONSE	MAIL DATE	DELIVER	DELIVERY MODE	
3 M(ONTHS	01/22/2007	PAPER		

Please find below and/or attached an Office communication concerning this application or proceeding.

If NO period for reply is specified above, the maximum statutory period will apply and will expire 6 MONTHS from the mailing date of this communication.

				3			
		Application No.	Applicant(s)				
Office Action Summary		10/642,611	AOYAGI ET AL.				
		Examiner www	Art Unit				
		Tod T. Van Roy	2828				
Period fe	The MAILING DATE of this communication aportion or Reply	opears on the cover sheet with the	he correspondence address				
WHIC - Exte after - If NC - Failt Any	CHEVER IS LONGER, FROM THE MAILING IS CHEVER IS LONGER, FROM THE MAILING IS CHEVER IS LONGER, FROM THE MAILING IS TO SIX (6) MONTHS from the mailing date of this communication. Of period for reply is specified above, the maximum statutory period ure to reply within the set or extended period for reply will, by stature ply received by the Office later than three months after the mailing patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUNICAT .136(a). In no event, however, may a reply to d will apply and will expire SIX (6) MONTHS te, cause the application to become ABAND	TON. De timely filed from the mailing date of this communication. ONED (35 U.S.C. § 133).				
Status							
1)⊠	Responsive to communication(s) filed on <u>03 l</u>	November 2006.	•				
2a)⊠	This action is FINAL. 2b) This action is non-final.						
3)[Since this application is in condition for allowed	ance except for formal matters,	prosecution as to the merits is				
	closed in accordance with the practice under	Ex parte Quayle, 1935 C.D. 11	, 453 O.G. 213.				
Disposit	ion of Claims						
4)🛛	Claim(s) 1,3 and 6-10 is/are pending in the a	pplication.					
	4a) Of the above claim(s) is/are withdra	awn from consideration.					
5)⊠	Claim(s) <u>7</u> is/are allowed.						
6)⊠	Claim(s) <u>1,3,6,8 and 9</u> is/are rejected.						
7)🖂	Claim(s) 10 is/are objected to.						
8)	Claim(s) are subject to restriction and/	or election requirement.					
Applicat	tion Papers						
9)[The specification is objected to by the Examin	ner.					
10)	The drawing(s) filed on is/are: a) ac	cepted or b) objected to by t	he Examiner.				
	Applicant may not request that any objection to the	e drawing(s) be held in abeyance.	See 37 CFR 1.85(a).				
	Replacement drawing sheet(s) including the corre	ction is required if the drawing(s) is	s objected to. See 37 CFR 1.121(d)).			
11)	The oath or declaration is objected to by the E	Examiner. Note the attached Of	fice Action or form PTO-152.				
Priority	under 35 U.S.C. § 119	·					
	Acknowledgment is made of a claim for foreig All b) Some * c) None of: 1. Certified copies of the priority document		9(a)-(d) or (f).				
	2. Certified copies of the priority documer		cation No.				
	3. Copies of the certified copies of the pri						
	application from the International Bure	·	• · · · · · · · · · · · · · · · · · · ·				
* ;	See the attached detailed Office action for a lis	• • • • • • • • • • • • • • • • • • • •	eived.				
Attachmei	nt(s)	•					
	ce of References Cited (PTO-892)		mary (PTO-413)				
	ce of Draftsperson's Patent Drawing Review (PTO-948) rmation Disclosure Statement(s) (PTO-1449 or PTO/SB/0		ail Date nal Patent Application (PTO-152)				
	er No(s)/Mail Date	6) Other:	11				

Art Unit: 2828

DETAILED ACTION

Response to Amendment

The examiner acknowledges the amending of claims 1,3, 6, and 8-10.

Response to Arguments

Applicant's arguments with respect to claim 1 have been considered but are moot in view of the new ground(s) of rejection.

The previous rejection of claim 1 over Abe in view of Lo is withdrawn due to the current amendment.

As per the remaining rejection to claim 1 over Abe in view of Lo and Lu:

The applicant has stated that the combination of Abe with Lo is un-obvious due to the fact that Abe teaches an edge emitter and Lo teaches a surface-emitting (SEL) device.

The examiner does agree with the applicant that the Abe and Lo references teach different emission types, but does not agree that the combination is un-obvious.

Lo teaches a SEL that uses both first and second order DFB type gratings (col.1 lines 12-37). Lo teaches the 2nd order gratings to be for out-coupling of the light, and the 1st order gratings to be used for feedback of the light (col.1 lines 12-37) to the interior of the device. Lo then teaches that strong coupling coefficients are beneficial in a number of different ways, including feedback (col.7 line 52 – col.8 line 8). These high values are taught to be possible due to the close proximity of the gain region (col.3 line 50 – col.4 line 10).

Abe teaches an edge emitting DFB type grating device wherein higher coupling coefficient values are used for feedback from a region in the device (col.12 lines 4-10) in order to output light from the opposite side. Abe further teaches that the values of the coupling coefficients are design elements chosen for particular devices (abs.).

Additionally, Abe teaches that the proximity to the gain region determines the strength of the coupling coefficient (col.6 line 61 – col.7 line 27), and the gratings are shown to be formed in close proximity to the gain regions in the disclosed embodiments (all figures).

As outlined above, both Abe and Lo teach their DFB gratings to be used for feedback of light to other regions of the devices. Although each device emits light in a different direction, each device utilizes similar gratings for the same purpose. Abe and Lo have also been shown to teach similar methods of gain to grating location in order to better tailor the coupling coefficient values. The examiner therefor believes that Abe and Lo are in fact related art pieces, and that using Lo to motivate a value of a coupling coefficient of a similar grating used for the same purpose is both reasonable and obvious to one of ordinary skill in the art.

Please see below for an updated rejection to the claims.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

Art Unit: 2828

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

The factual inquiries set forth in *Graham* v. *John Deere Co.*, 383 U.S. 1, 148 USPQ 459 (1966), that are applied for establishing a background for determining obviousness under 35 U.S.C. 103(a) are summarized as follows:

- 1. Determining the scope and contents of the prior art.
- 2. Ascertaining the differences between the prior art and the claims at issue.
- 3. Resolving the level of ordinary skill in the pertinent art.
- 4. Considering objective evidence present in the application indicating obviousness or nonobviousness.

Claims 1, and 8 are rejected under 35 U.S.C. 103(a) as being unpatentable over Abe et al. (US 5020072) in view of Lo (US 5617436), and further in view of Lu et al. ("High Power and High Speed Performance of 1.3um Strained MQW Gain Coupled DFB Lasers," IEEE JQE, Vol.1, No.2 1995, pgs.375-381).

With respect to claim 1, Abe teaches a refractive index coupling distributed feedback (DFB) semiconductor laser comprising opposed first and second end surfaces through which light generated within the semiconductor laser may be emitted (fig.4 left and right sides), a central phase shift structure located substantially centrally between the first and second end surfaces (col.9 lines 4-7), and first and second diffraction gratings respectively extending from the central phase shift structure to the first and second end faces (fig.4e), an average coupling coefficient k2 of a diffraction grating on one end face side (fig.4 right side) is smaller than an average coupling coefficient k1 of a diffraction grating on the other end face side (fig.4 left side) (col.12 lines 4-10). Abe does not teach the absolute value of the real part of the coupling coefficient to be at

Art Unit: 2828

least 4 times the absolute value of the imaginary part of the coupling coefficient, or the coupling coefficients to be greater than 100cm-1. Lo teaches a DFB semiconductor laser device (fig.1) in which the coupling coefficients are greater than 100cm-1 (col.4 lines 11-21). Lu teaches a complex coupled DFB laser in which a real part of a coupling coefficient is at least 4 times an imaginary part of a coupling coefficient (Fig.2, col.3 lines 22-29, where the figure and text describe utilizing real and imaginary components of ratios less than 25%). It would have been obvious to one of ordinary skill in the art at the time of the invention to combine the DFB laser of Abe with the large coupling coefficients of Lo in order to increase resonator feedback, utilizing more gain, and allow for the reduction of the laser spot size (col.4 lines 22-25), as well as to combine the DFB laser with complex coupling of Lu in order to have less sensitivity to external reflections (Lu, col.1 lines 14-20) and to provide for enhanced single mode operation (Lu, col.3 lines 24-29).

With respect to claim 8, Abe and Lo teach the DFB device outlined in the rejection to claim 1 and further teach changing the coupling coefficients, k1 and k2, via changing a thickness of a low refractive index layer between that of the active region and the high index grating portion (fig.7, col.11 lines 49-57).

Claim 3 is rejected under 35 U.S.C. 103(a) as being unpatentable over Abe et al. in view of Lo and further in view of Lu and Huang (US 6574261).

With respect to claim 3, Abe, Lu and Lo teach the DFB device outlined in the rejection to claim 1, but do not teach the device to include a plurality of phase shift

Art Unit: 2828

structures located at substantially symmetrical positions with respect to the central phase sift portion in the diffraction gratings. Huang teaches a DFB semiconductor laser utilizing multiple phase shift structures (fig.9), located at substantially symmetrical positions with respect to the central phase sift portion in the diffraction gratings. It would have been obvious to one of ordinary skill in the art at the time of the invention to combine the DFB laser of Abe, Lu and Lo with the multiple phase shift structures of Huang in order to uniformly distribute carriers and reduce spatial hole burning (Huang, col.12 lines 47-50).

Claim 6 is rejected under 35 U.S.C. 103(a) as being unpatentable over Abe et al. in view of Lo and further in view of Lu and Takahashi et al. (US 5727015).

With respect to claim 6, Abe, Lu and Lo teach the DFB device outlined in the rejection to claim 1, but do not teach the device to have a higher ratio of higher index material to lower index material in the k1 region than in the k2 region. Takahashi teaches DFB semiconductor laser in which the duty of the gratings is examined based on coupling coefficient values (fig.3a, in which it can be understood that a high coupling region, k1, could have a larger duty than a low coupling region, k2, this duty being defined as the length of the higher index region to the lower index region, col.1 lines 63-67, fig.1- comparing higher index #106 to lower index #108 as analyzed in fig.3a). It would have been obvious to one of ordinary skill in the art at the time of the invention to combine the DFB laser of Abe, Lu and Lo with the high to low duty values of Huang in order to appropriately couple the E-field to a desired grating region.

Art Unit: 2828

Claim 9 is rejected under 35 U.S.C. 103(a) as being unpatentable over Abe et al. in view of Lo and further in view of Lu and Weber (US 5379318).

With respect to claim 9, Abe, Lu and Lo teach the DFB device outlined in the rejection to claim 1, but do not teach the device to satisfy the relationship that the effective index through grating2 times the period of grating2 be almost equal to the effective index of grating1 times the period of grating1. Weber teaches a semiconductor laser in which an effective index through a grating2 times the period of a grating2 be almost equal to the effective index of a grating1 times the period of a grating1 (fig. 1 #G1,G3; the effective index of G3 would be greater than that of G1 due to the larger amount of high index grating material, but the period of G1 would be greater than that of G3 in order to correctly fit the relationship shown in fig.2, this leads to the approximate balancing of NeffG1*PeriodG1 almost equal to NeffG3*PeriodG3). It would have been obvious to one of ordinary skill in the art at the time of the invention to combine the DFB laser of Abe, Sato and Lo with the grating structure of Weber in order to allow for a larger degree of wavelength selectivity.

Allowable Subject Matter

Claim 10 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Art Unit: 2828

The following is a statement of reasons for the indication of allowable subject matter:

Claim 10 is allowable for the same reasons outlined in the previous advisory action (paper no 02012006) as it is largely a duplicate of former claim 2.

Conclusion

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Tod T. Van Roy whose telephone number is (571)272-8447. The examiner can normally be reached on M-F.

Art Unit: 2828

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Minsun Harvey can be reached on (571)272-1835. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

TVR

MINSUN OH HARVEY PRIMARY EXAMINER